

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

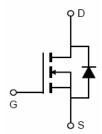
General Features

- V_{DS} =120V, I_D =63A $R_{DS(ON)}$ =11.5m Ω , typical (TO-220)@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP12N12	NCEP12N12	TO-220	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	120	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	63	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	45	Α
Pulsed Drain Current	I _{DM}	252	Α
Maximum Power Dissipation	P _D	100	W
Derating factor		0.67	W/℃
Single pulse avalanche energy (Note 4)	E _{AS}	288	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	R ₀ JC	1.5	°C/W	l
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

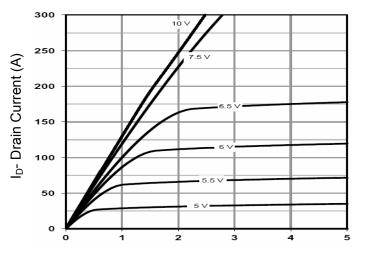
Parameter	Symbol Condition		Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	120		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V,V _{GS} =0V	V _{DS} =120V,V _{GS} =0V -		1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =31.5A	-	11.5	12.5	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =31.5A		50	-	S
Dynamic Characteristics (Note3)	·					
Input Capacitance	C _{lss}	V -00VV -0V	-	2230	-	pF
Output Capacitance	C _{oss}	V_{DS} =60V, V_{GS} =0V, F=1.0MHz		170	-	pF
Reverse Transfer Capacitance	C _{rss}			19	-	pF
Switching Characteristics (Note 3)	·					
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	t _r	V_{DD} =60 V , I_{D} =31.5 A	-	9	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	29	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Qg	\/ -60\/ -21.54	-	45	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =60V, I_{D} =31.5A, V_{GS} =10V	-	15	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} -10V	-	14.5	-	nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 2)	V _{SD}	V _{GS} =0V,I _S =31.5A	-	-	1.2	V
Diode Forward Current	Is		-	-	63	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = 31.5A$	-	55	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	98	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 3. Guaranteed by design, not subject to production
- 4. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.25mH,Rg=25 Ω

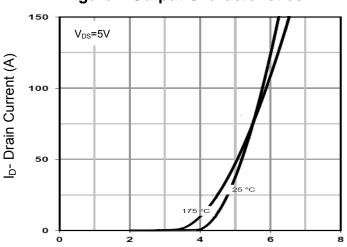


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V) **Figure 2 Transfer Characteristics**

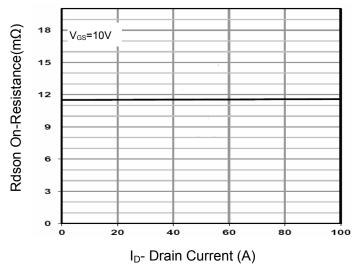


Figure 3 Rdson- Drain Current

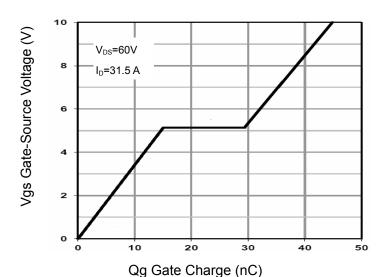


Figure 4 Gate Charge

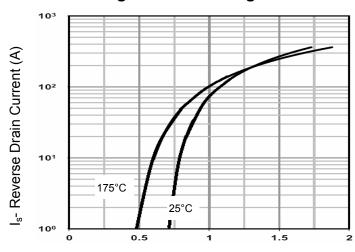


Figure 5 Source- Drain Diode Forward

Vsd Source-Drain Voltage (V)

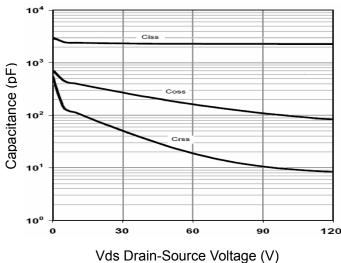
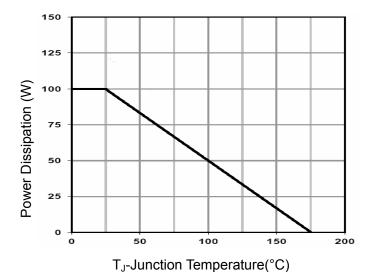


Figure 6 Capacitance vs Vds





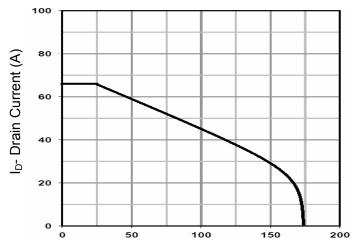
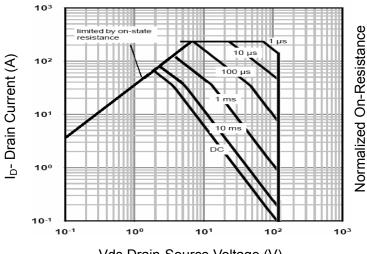


Figure 7 Power De-rating

T_J-Junction Temperature (°C) **Figure 9 Current De-rating**



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

Figure 10 Rdson-Junction Temperature

T_J-Junction Temperature(°C)

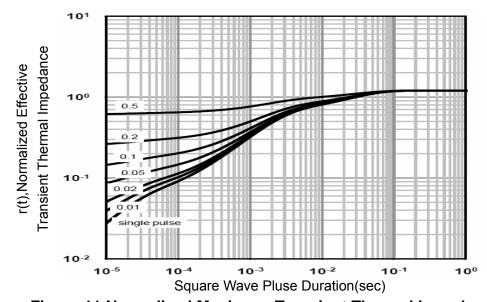
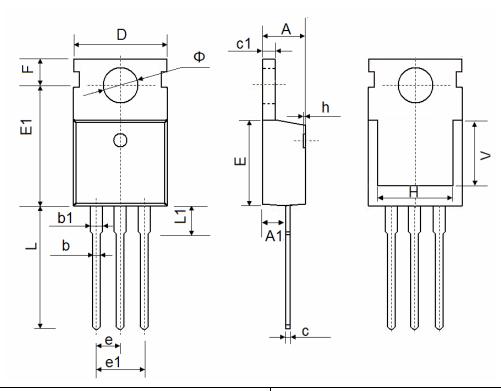


Figure 11 Normalized Maximum Transient Thermal Impedance

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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900) REF. 0		276 REF.	
Ф	3.400	3.800	0.134	0.150	



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